

LMK60XX 高性能低ジッタ発振器

1 特長

- 低ノイズ、高性能
 - ジッタ: 150fs RMS (標準値)、 $F_{out} > 100\text{MHz}$
 - PSRR: -60dBc 、堅牢な電源ノイズ耐性
- 対応出力フォーマット
 - LVPECLおよびLVDS: 最高800MHz
 - HCSL: 最大400MHz
- 合計周波数公差: $\pm 50\text{ppm}$ (LMK60X2)、 $\pm 25\text{ppm}$ (LMK60X0)
- 動作電圧: 3.3V
- 工業用温度範囲: $-40^{\circ}\text{C} \sim +85^{\circ}\text{C}$
- 7mmx 5mmの6ピン・パッケージ、業界標準の7050 XOパッケージとピン互換

2 アプリケーション

- 水晶振動子、SAW、またはシリコン・ベースの発振器に代わる高性能の代替品
- スイッチ、ルータ、ネットワーク・ライン・カード、ベースバンド・ユニット(BBU)、サーバ、ストレージ/SAN
- 試験/測定機器
- 医療用画像処理
- FPGA、プロセッサ接続

3 概要

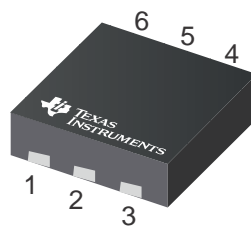
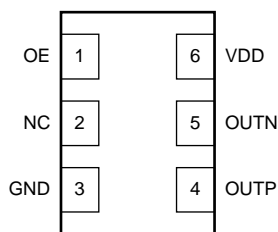
LMK60XXデバイスは低ジッタの発振器で、一般的に使用されるリファレンス・クロックを生成します。このデバイスは、任意のリファレンス・クロック周波数をサポートするよう工場であらかじめプログラムされ、出力フォーマットとしてLVPECLおよびLVDSで最高800MHz、HCSLで最高400MHzをサポートします。内部的な電力コンディショニングにより、電源リップル除去(PSRR)が非常に優れているため、電力供給ネットワークのコストと複雑性を減らすことができます。単一の $3.3\text{V} \pm 5\%$ 電源で動作します。

製品情報⁽¹⁾

型番	出力周波数 (MHz)とフォーマット	総合周波数安定性(ppm)	パッケージサイズ
LMK60E2-150M	150 LVPECL	± 50	6ピンQFM、7mmx5mm
LMK60E0-156257	156.257 LVPECL	± 25	
LMK60A0-148351	148 + 32/91 LVDS	± 25	
LMK60A0-148M	148.5 LVDS	± 25	

(1) 利用可能なすべてのパッケージについては、このデータシートの末尾にある注文情報を参照してください。

ピン配置



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4 改訂履歴

Revision B (December 2016) から Revision C に変更

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Revision A (August 2016) から Revision B に変更

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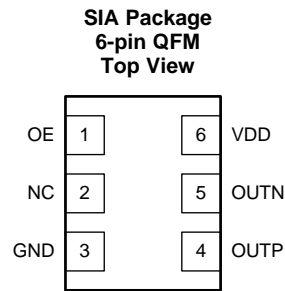
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2016年6月発行のものから更新

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5 Pin Configuration and Functions



Pin Functions

PIN		I/O	DESCRIPTION
NAME	NO.		
POWER			
GND	3	Ground	Device ground
VDD	6	Analog	3.3-V power supply
OUTPUT BLOCK			
OUTP, OUTN	4, 5	Universal	Differential output pair (LVPECL, LVDS or HCSSL).
DIGITAL CONTROL / INTERFACES			
NC	2	N/A	No connect
OE	1	LVC MOS	Output enable (internal pullup). When set to low, output pair is disabled and set at high impedance.

6 Specifications

6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)⁽¹⁾

		MIN	MAX	UNIT
VDD	Device supply voltage	-0.3	3.6	V
V _{IN}	Output voltage for logic inputs	-0.3	VDD + 0.3	V
V _{OUT}	Output voltage for clock outputs	-0.3	VDD + 0.3	V
T _J	Junction temperature		150	°C
T _{STG}	Storage temperature	-40	125	°C

- (1) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions*. Exposure to absolute maximum-rated conditions for extended periods may affect device reliability.

6.2 ESD Ratings

		VALUE	UNIT
V _(ESD)	Electrostatic discharge	Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001 ⁽¹⁾	±2000
		Charged-device model (CDM), per JEDEC specification JESD22-C101 ⁽²⁾	±500

(1) JEDEC document JEP155 states that 500 V HBM allows safe manufacturing with a standard ESD control process.

(2) JEDEC document JEP157 states that 250 V CDM allows safe manufacturing with a standard ESD control process.

6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

		MIN	NOM	MAX	UNIT
VDD	Device supply voltage	3.135	3.3	3.465	V
T _A	Ambient temperature	-40	25	85	°C
T _J	Junction temperature			120	°C
t _{RAMP}	VDD power-up ramp time	0.1		100	ms

6.4 Thermal Information

THERMAL METRIC ⁽¹⁾	LMK60XX ^{(2) (3) (4)}			UNIT	
	SIA (QFM)				
	6 PINS				
	Airflow (LFM) 0	Airflow (LFM) 200	Airflow (LFM) 400		
R _{θJA}	Junction-to-ambient thermal resistance	55.2	46.4	43.7	°C/W
R _{θJC(top)}	Junction-to-case (top) thermal resistance	34.6	n/a	n/a	°C/W
R _{θJB}	Junction-to-board thermal resistance	37.7	n/a	n/a	°C/W
ψ _{JT}	Junction-to-top characterization parameter	11.3	17.6	22.5	°C/W
ψ _{JB}	Junction-to-board characterization parameter	37.7	41.5	40.1	°C/W
R _{θJC(bot)}	Junction-to-case (bottom) thermal resistance	n/a	n/a	n/a	°C/W

- (1) For more information about traditional and new thermal metrics, see the [Semiconductor and IC Package Thermal Metrics](#) application report.
- (2) The package thermal resistance is calculated on a 4 layer JEDEC board.
- (3) Connected to GND with 3 thermal vias (0.3-mm diameter).
- (4) ψ_{JB} (junction to board) is used when the main heat flow is from the junction to the GND pad. See the [Layout Guidelines](#) section for more information on ensuring good system reliability and quality.

6.5 Electrical Characteristics - Power Supply⁽¹⁾

VDD = 3.3 V ± 5%, T_A = -40C to 85°C

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT	
IDD	Device current consumption	LVPECL ⁽²⁾	162	208	mA	
			LVDS	152		196
			HCSL	155		196
IDD-PD	Device current consumption when output is disabled	OE = GND	136		mA	

- (1) Refer to [Parameter Measurement Information](#) for relevant test conditions.
- (2) On-chip power dissipation should exclude 40 mW, dissipated in the 150 Ω termination resistors, from total power dissipation.

6.6 LVPECL Output Characteristics⁽¹⁾

VDD = 3.3 V ± 5%, T_A = -40C to 85°C

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
f _{OUT}	Output frequency ⁽²⁾	10		800	MHz
V _{OD}	Output voltage swing (V _{OH} – V _{OL}) ⁽²⁾	700	800	1200	mV
V _{OUT, DIFF, PP}	Differential output peak-to-peak swing		2 × V _{OD}		V
V _{OS}	Output common-mode voltage		VDD – 1.55		V
t _R / t _F	Output rise/fall time (20% to 80%) ⁽³⁾		150	250	ps
ODC	Output duty cycle ⁽³⁾	45%		55%	

- (1) Refer to [Parameter Measurement Information](#) for relevant test conditions.
- (2) An output frequency over f_{OUT} max spec is possible, but output swing may be less than V_{OD} min spec.
- (3) Ensured by characterization.

6.7 LVDS Output Characteristics⁽¹⁾

VDD = 3.3 V ± 5%, T_A = -40°C to 85°C

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
f _{OUT}	Output frequency ⁽¹⁾		10		800	MHz
V _{OD}	Output voltage swing (V _{OH} - V _{OL}) ⁽¹⁾		300	390	480	mV
V _{OUT, DIFF, PP}	Differential output peak-to-peak swing		2 × V _{OD}			V
V _{OS}	Output common-mode voltage		1.2			V
t _R / t _F	Output rise/fall time (20% to 80%) ⁽²⁾		150		250	ps
ODC	Output duty cycle ⁽²⁾		45%		55%	
R _{OUT}	Differential output impedance		125			Ω

(1) An output frequency over f_{OUT} max spec is possible, but output swing may be less than V_{OD} min spec.

(2) Ensured by characterization.

6.8 HCSL Output Characteristics⁽¹⁾

VDD = 3.3 V ± 5%, T_A = -40°C to 85°C

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
f _{OUT}	Output frequency		10		400	MHz
V _{OH}	Output high voltage		600		850	mV
V _{OL}	Output low voltage		-100		100	mV
V _{CROSS}	Absolute crossing voltage ⁽²⁾⁽³⁾		250		475	mV
V _{CROSS-DELTA}	Variation of V _{CROSS} ⁽²⁾⁽³⁾		0		140	mV
dV/dt	Slew rate ⁽⁴⁾		0.8		2	V/ns
ODC	Output duty cycle ⁽⁴⁾		45%		55%	

(1) Refer to [Parameter Measurement Information](#) for relevant test conditions.

(2) Measured from -150 mV to +150 mV on the differential waveform with the 300 mVpp measurement window centered on the differential zero crossing.

(3) Ensured by design.

(4) Ensured by characterization.

6.9 OE Input Characteristics

VDD = 3.3 V ± 5%, T_A = -40°C to 85°C

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
V _{IH}	Input high voltage		1.4			V
V _{IL}	Input low voltage				0.6	V
I _{IH}	Input high current	V _{IH} = VDD	-40		40	μA
I _{IL}	Input low current	V _{IL} = GND	-40		40	μA
C _{IN}	Input capacitance			2		pF

6.10 Frequency Tolerance Characteristics⁽¹⁾

VDD = 3.3 V ± 5%, T_A = -40°C to 85°C

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
f _T	Total frequency tolerance	LMK60X2: All output formats, frequency bands and device junction temperature up to 125°C; includes initial freq tolerance, temperature & supply voltage variation, solder reflow and aging (10 years)	-50		50	ppm
		LMK60X0: All output formats, frequency bands and device junction temperature up to 115°C; includes initial freq tolerance, temperature & supply voltage variation, solder reflow and aging (5 years at 40°C)	-25		25	ppm

(1) Ensured by characterization.

6.11 Power-On/Reset Characteristics (VDD)

VDD = 3.3 V ± 5%, T_A = -40°C to 85°C

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT	
V _{THRESH}	Threshold voltage ⁽¹⁾	2.72		2.95	V	
V _{DROOP}	Allowable voltage droop ⁽²⁾			0.1	V	
t _{STARTUP}	Start-up time ⁽¹⁾	Time elapsed from VDD at 3.135 V to output enabled			10	ms
t _{OE-EN}	Output enable time ⁽²⁾	Time elapsed from OE at V _{IH} to output enabled			50	µs
t _{OE-DIS}	Output disable time ⁽²⁾	Time elapsed from OE at V _{IL} to output disabled			50	µs

- (1) Ensured by characterization.
 (2) Ensured by design.

6.12 PSRR Characteristics⁽¹⁾

VDD = 3.3 V, T_A = 25°C, FS[1:0] = NC, NC

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
PSRR	Sine wave at 50 kHz		-60		dBc
	Sine wave at 100 kHz		-60		
	Sine wave at 500 kHz		-60		
	Sine wave at 1 MHz		-60		

- (1) Refer to Parameter Measurement Information for relevant test conditions.
 (2) Measured max spur level with 50 mVpp sinusoidal signal between 50 kHz and 1 MHz applied on VDD pin
 (3) $DJ_{SPUR} (ps, pk-pk) = [2 \cdot 10 \cdot (SPUR/20) / (\pi \cdot f_{OUT})] \cdot 1e6$, where PSRR or SPUR in dBc and f_{OUT} in MHz.

6.13 PLL Clock Output Jitter Characteristics⁽¹⁾⁽²⁾

VDD = 3.3 V ± 5%, T_A = -40°C to 85°C

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
RJ	RMS phase jitter ⁽³⁾ (12 kHz – 20 MHz)	f _{OUT} ≥ 100 MHz, All output types			fs RMS

- (1) Refer to Parameter Measurement Information for relevant test conditions.
 (2) Phase jitter measured with Agilent E5052 signal source analyzer using a differential-to-single ended converter (balun or buffer).
 (3) Ensured by characterization.

6.14 Additional Reliability and Qualification

PARAMETER	CONDITION / TEST METHOD
Mechanical Shock	MIL-STD-202, Method 213
Mechanical Vibration	MIL-STD-202, Method 204
Moisture Sensitivity Level	J-STD-020, MSL3

6.15 Typical Characteristics

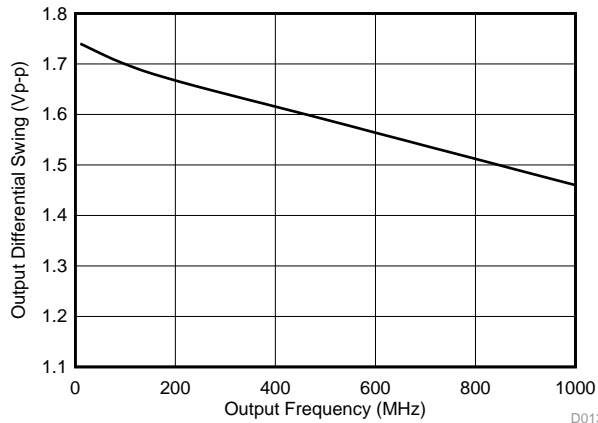


Figure 1. LVPECL Differential Output Swing vs Frequency

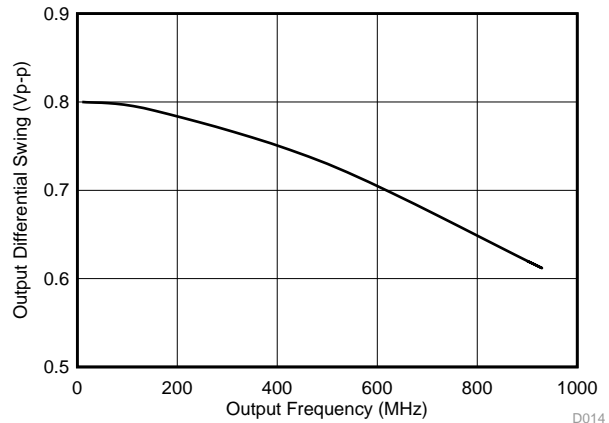


Figure 2. LVDS Differential Output Swing vs Frequency

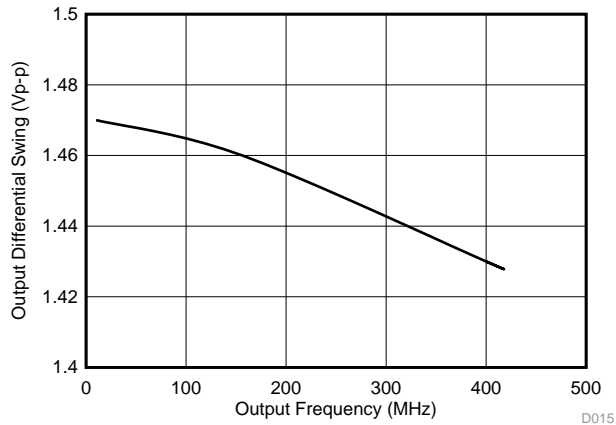


Figure 3. HCSL Differential Output Swing vs Frequency

7 Parameter Measurement Information

7.1 Device Output Configurations

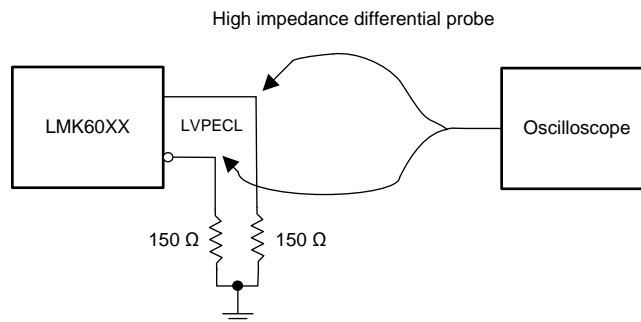


Figure 4. LVPECL Output DC Configuration During Device Test

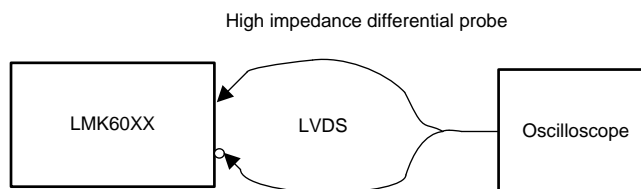


Figure 5. LVDS Output DC Configuration During Device Test

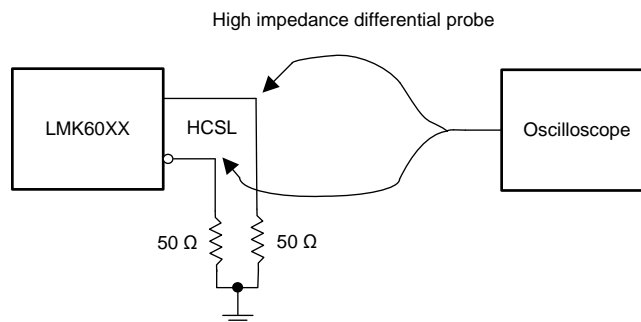


Figure 6. HCSL Output DC Configuration During Device Test

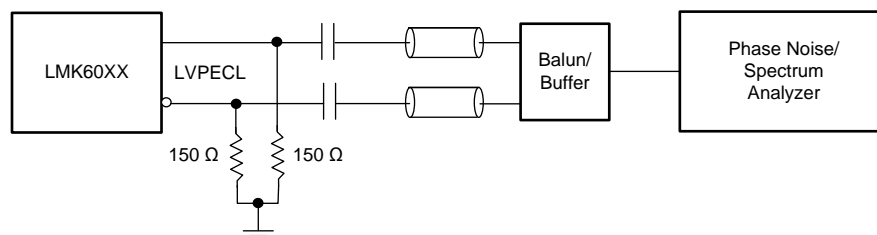


Figure 7. LVPECL Output AC Configuration During Device Test

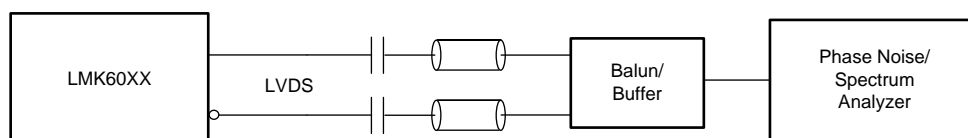


Figure 8. LVDS Output AC Configuration During Device Test

Device Output Configurations (continued)

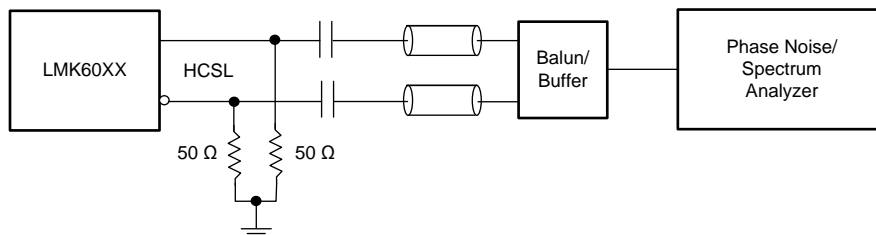


Figure 9. HCSL Output AC Configuration During Device Test

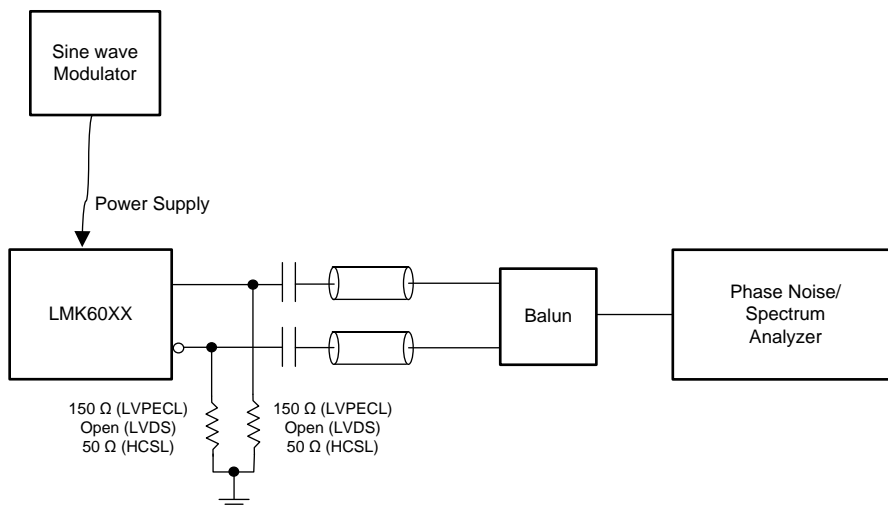


Figure 10. PSRR Test Setup

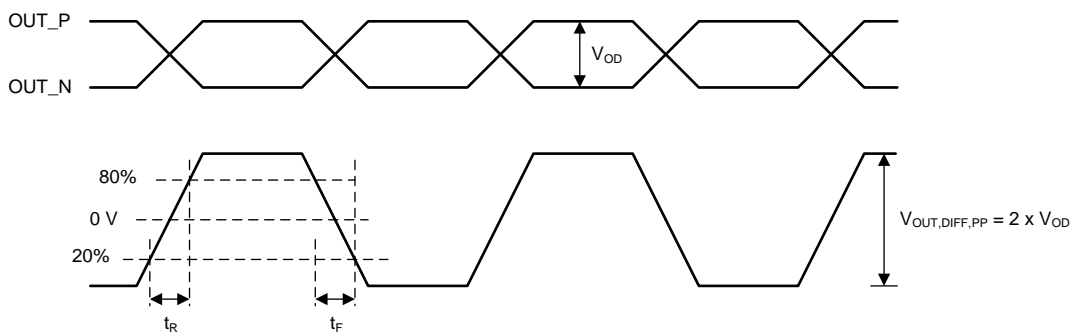


Figure 11. Differential Output Voltage and Rise/Fall Time

8 Power Supply Recommendations

For best electrical performance of LMK60XX, TI recommends using a combination of 10 μF , 1 μF and 0.1 μF on its power supply bypass network. TI also recommends using component side mounting of the power supply bypass capacitors, and it is best to use 0201 or 0402 body size capacitors to facilitate signal routing. Keep the connections between the bypass capacitors and the power supply on the device as short as possible. Ground the other side of the capacitor using a low impedance connection to the ground plane. [Figure 12](#) shows the layout recommendation for power supply decoupling of LMK60XX.

9 Layout

9.1 Layout Guidelines

The following sections provides recommendations for board layout, solder reflow profile and power supply bypassing when using LMK60XX to ensure good thermal / electrical performance and overall signal integrity of entire system.

9.1.1 Ensuring Thermal Reliability

The LMK60XX is a high performance device. Therefore pay careful attention to device configuration and printed-circuit board (PCB) layout with respect to power consumption. The ground pin needs to be connected to the ground plane of the PCB through three vias or more, as shown in [Figure 12](#), to maximize thermal dissipation out of the package.

[Equation 1](#) describes the relationship between the PCB temperature around the LMK60XX and its junction temperature.

$$T_B = T_J - \Psi_{JB} * P$$

where

- T_B : PCB temperature around the LMK60XX
 - T_J : Junction temperature of LMK60XX
 - Ψ_{JB} : Junction-to-board thermal resistance parameter of LMK60XX (37.7°C/W without airflow)
 - P : On-chip power dissipation of LMK60XX
- (1)

To ensure that the maximum junction temperature of LMK60XX is below 120°C, it can be calculated that the maximum PCB temperature without airflow should be at 90°C or below when the device is optimized for best performance resulting in maximum on-chip power dissipation of 0.68 W.

9.1.2 Best Practices for Signal Integrity

For best electrical performance and signal integrity of entire system with LMK60XX, TI recommends routing vias into decoupling capacitors and then into the LMK60XX. TI also recommends increasing the via count and width of the traces wherever possible. These steps ensure lowest impedance and shortest path for high-frequency current flow. [Figure 12](#) shows the layout recommendation for LMK60XX.

Layout Guidelines (continued)

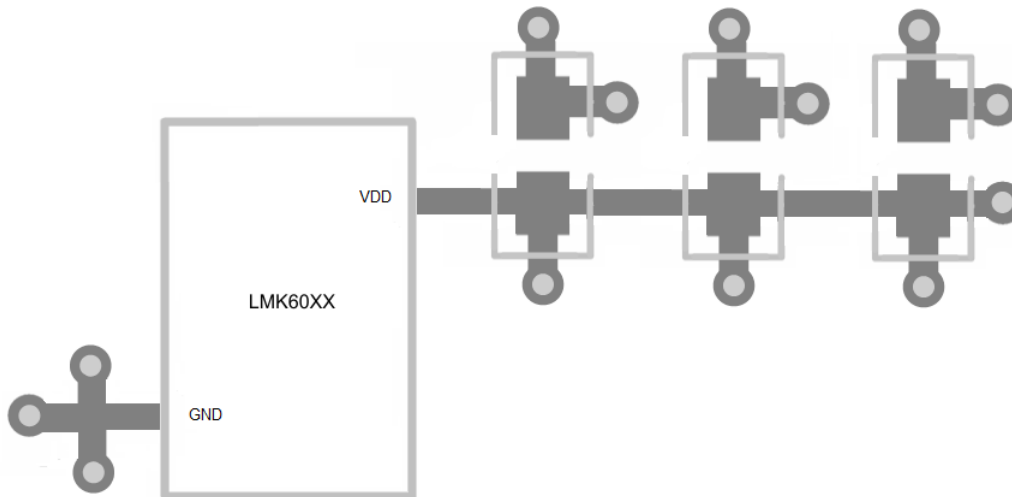


Figure 12. LMK60XX Layout Recommendation for Power Supply and Ground

9.1.3 Recommended Solder Reflow Profile

TI recommends following the solder paste supplier's recommendations to optimize flux activity and to achieve proper melting temperatures of the alloy within the guidelines of J-STD-20. It is preferable for the LMK60XX to be processed with the lowest peak temperature possible while also remaining below the components peak temperature rating as listed on the MSL label. The exact temperature profile would depend on several factors including maximum peak temperature for the component as rated on the MSL label, Board thickness, PCB material type, PCB geometries, component locations, sizes, densities within PCB, as well solder manufactures recommended profile, and capability of the reflow equipment to as confirmed by the SMT assembly operation.

10 デバイスおよびドキュメントのサポート

10.1 関連リンク

次の表に、クイック・アクセス・リンクを示します。カテゴリには、技術資料、サポートおよびコミュニティ・リソース、ツールとソフトウェア、およびサンプル注文またはご購入へのクイック・アクセスが含まれます。

表 1. 関連リンク

製品	プロダクト・フォルダ	サンプルとご購入	技術資料	ツールとソフトウェア	サポートとコミュニティ
LMK60E2-150M	ここをクリック	ここをクリック	ここをクリック	ここをクリック	ここをクリック
LMK60E0-156257	ここをクリック	ここをクリック	ここをクリック	ここをクリック	ここをクリック

10.2 ドキュメントの更新通知を受け取る方法

ドキュメントの更新についての通知を受け取るには、[ti.com](#)のデバイス製品フォルダを開いてください。右上の隅にある「通知を受け取る」をクリックして登録すると、変更されたすべての製品情報に関するダイジェストを毎週受け取れます。変更の詳細については、修正されたドキュメントに含まれている改訂履歴をご覧ください。

10.3 コミュニティ・リソース

The following links connect to TI community resources. Linked contents are provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's [Terms of Use](#).

TI E2E™オンライン・コミュニティ *TIのE2E (Engineer-to-Engineer)* コミュニティ。エンジニア間の共同作業を促進するために開設されたものです。e2e.ti.comでは、他のエンジニアに質問し、知識を共有し、アイデアを検討して、問題解決に役立てることができます。

設計サポート *TIの設計サポート* 役に立つE2Eフォーラムや、設計サポート・ツールをすばやく見つけることができます。技術サポート用の連絡先情報も参照できます。

10.4 商標

E2E is a trademark of Texas Instruments.
 All other trademarks are the property of their respective owners.

10.5 静電気放電に関する注意事項



これらのデバイスは、限定的なESD(静電破壊)保護機能を内蔵しています。保存時または取り扱い時は、MOSゲートに対する静電破壊を防止するために、リード線同士をショートさせておくか、デバイスを導電フォームに入れる必要があります。

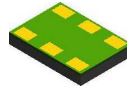
10.6 Glossary

[SLYZ022](#) — *TI Glossary*.

This glossary lists and explains terms, acronyms, and definitions.

11 メカニカル、パッケージ、および注文情報

以降のページには、メカニカル、パッケージ、および注文に関する情報が記載されています。この情報は、そのデバイスについて利用可能な最新のデータです。このデータは予告なく変更されることがあり、ドキュメントが改訂される場合もあります。本データシートのブラウザ版を使用されている場合は、画面左側の説明をご覧ください。

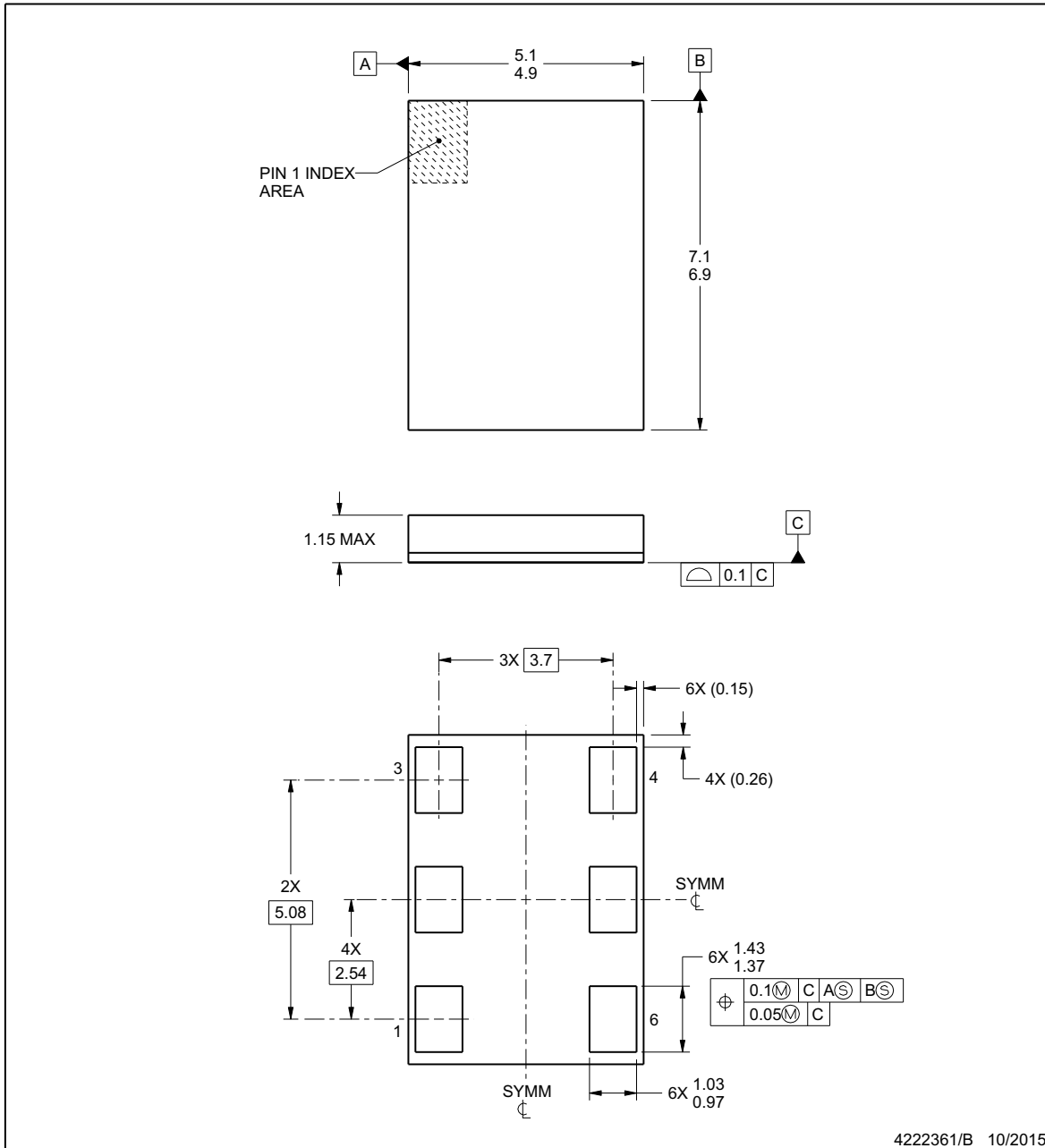


PACKAGE OUTLINE

SIA0006A

QFM - 1.15 mm max height

QUAD FLAT MODULE



NOTES:

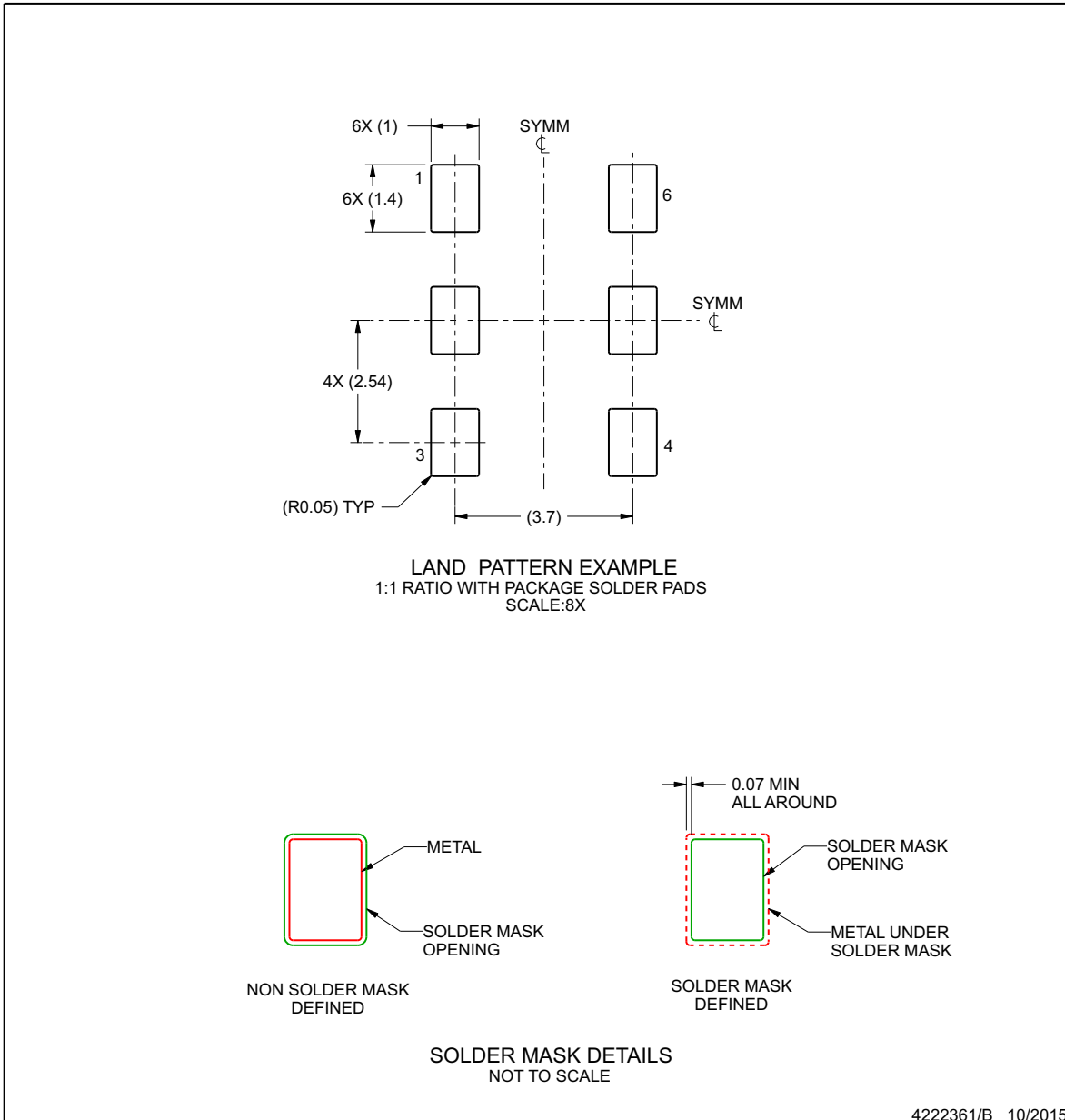
1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.

EXAMPLE BOARD LAYOUT

SIA0006A

QFM - 1.15 mm max height

QUAD FLAT MODULE



NOTES: (continued)

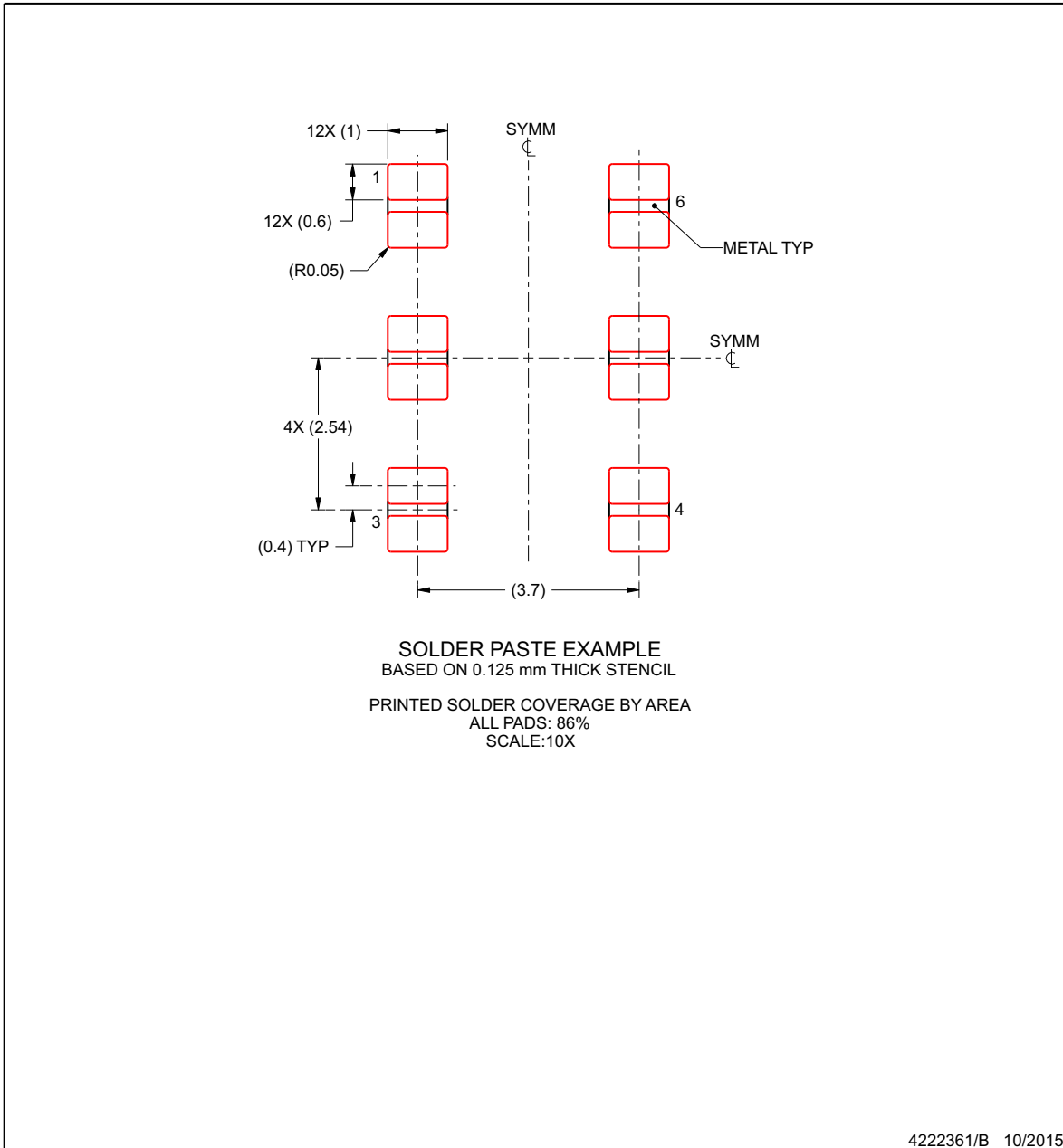
3. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/slua271).

EXAMPLE STENCIL DESIGN

SIA0006A

QFM - 1.15 mm max height

QUAD FLAT MODULE



NOTES: (continued)

4. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
LMK60A0-148M35SIAR	NRND	QFM	SIA	6	2500	RoHS & Green	NIAU	Level-3-260C-168 HR	-40 to 85	LMK60A0 148M35	
LMK60A0-148M35SIAT	NRND	QFM	SIA	6	250	RoHS & Green	NIAU	Level-3-260C-168 HR	-40 to 85	LMK60A0 148M35	
LMK60A0-148M50SIAR	NRND	QFM	SIA	6	2500	RoHS & Green	NIAU	Level-3-260C-168 HR	-40 to 85	LMK60A0 148M50	
LMK60A0-148M50SIAT	NRND	QFM	SIA	6	250	RoHS & Green	NIAU	Level-3-260C-168 HR	-40 to 85	LMK60A0 148M50	
LMK60E0-156257SIAR	ACTIVE	QFM	SIA	6	2500	RoHS & Green	NIAU	Level-3-260C-168 HR	-40 to 85	LMK60E0 156257	Samples
LMK60E0-156257SIAT	ACTIVE	QFM	SIA	6	250	RoHS & Green	NIAU	Level-3-260C-168 HR	-40 to 85	LMK60E0 156257	Samples
LMK60E2-150M00SIAR	NRND	QFM	SIA	6	2500	RoHS & Green	NIAU	Level-3-260C-168 HR	-40 to 85	LMK60E2 150M00	
LMK60E2-150M00SIAT	NRND	QFM	SIA	6	250	RoHS & Green	NIAU	Level-3-260C-168 HR	-40 to 85	LMK60E2 150M00	

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSELETE: TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

⁽⁵⁾ Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

⁽⁶⁾ Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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